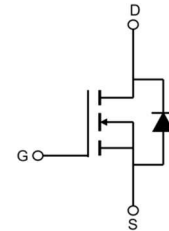


AP30P06

P-Channel Enhancement Mosfet

Feature

- -60V,-30A
 $R_{DS(ON)} < 30m\Omega @ V_{GS} = -10V$ TYP:23 m Ω
 $R_{DS(ON)} < 38m\Omega @ V_{GS} = -4.5V$ TYP:27 m Ω
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
30P06	AP30P06	TO-220	-	-	1000

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	-30	A
Continuous Drain Current ($T_a = 100^\circ\text{C}$)	I_D	-20	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-120	A
Singel Pulsed Avalanche Energy ⁽²⁾	E_{AS}	90	mJ
Power Dissipation	P_D	90	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.25	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

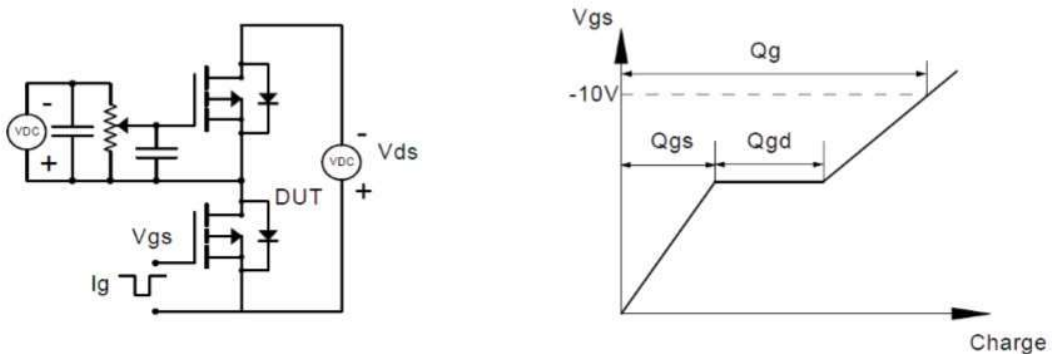
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.7	-2.5	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -15A$	-	23	30	m Ω
		$V_{GS} = -4.5V, I_D = -10A$	-	27	38	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$	-	2400	-	pF
Output Capacitance	C_{oss}		-	251	-	
Reverse Transfer Capacitance	C_{rss}		-	196	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -30V, I_D = -30A, R_L = 3\Omega$ $V_{GS} = -10V, R_G = 3\Omega$	-	15	-	ns
Turn-on rise time	t_r		-	120	-	
Turn-off delay time	$t_{d(off)}$		-	245	-	
Turn-off fall time	t_f		-	199	-	
Total Gate Charge	Q_g	$V_{DS} = -30V, I_D = -15A,$ $V_{GS} = -10V$	-	49	-	nC
Gate-Source Charge	Q_{gs}		-	8	-	
Gate-Drain Charge	Q_{gd}		-	12	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V_{DS}	$V_{GS} = 0V, I_S = -10A$	-	-	-1.2	V
Diode Forward current ⁽³⁾	I_S		-	-	-30	A

Notes:

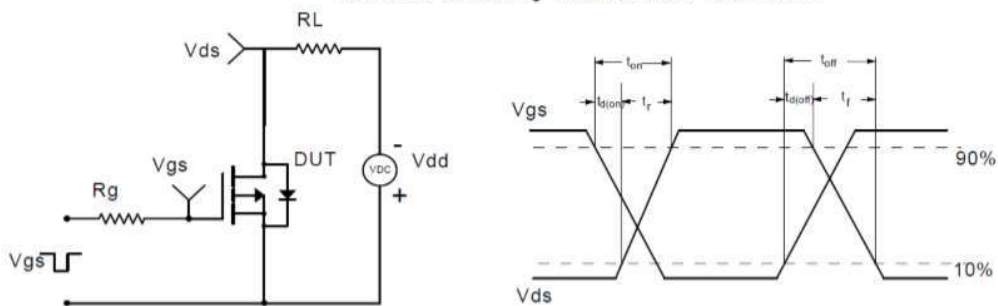
1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: $T_J = 25^\circ\text{C}, V_{DD} = -30V, R_G = 20\Omega, L = 0.5\text{mH}$
3. Pulse Test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
4. Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$

Test Circuit

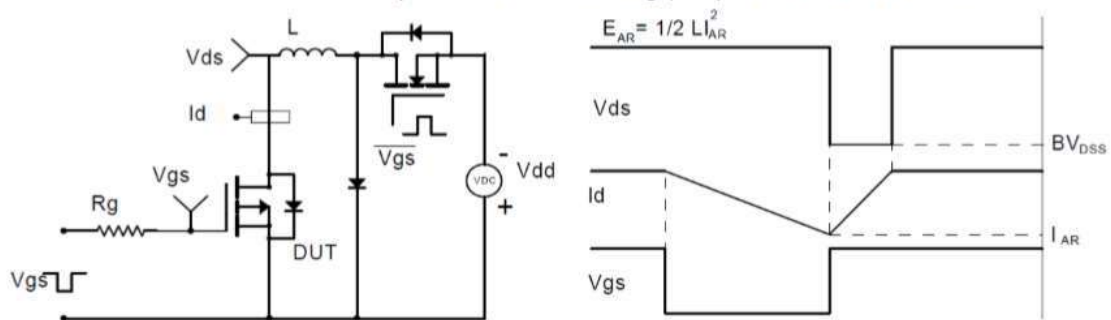
Gate Charge Test Circuit & Waveform



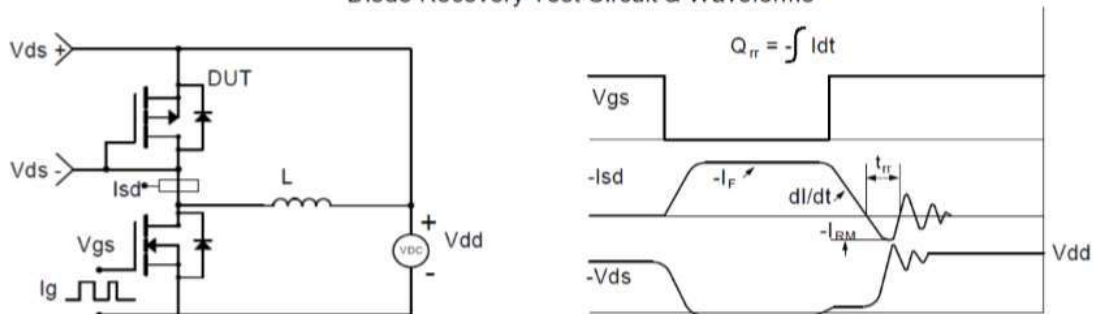
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Performance Characteristics

Figure 1: Output Characteristics

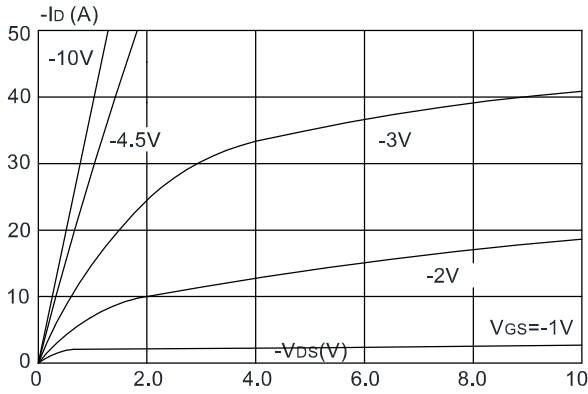


Figure 2: Typical Transfer Characteristics

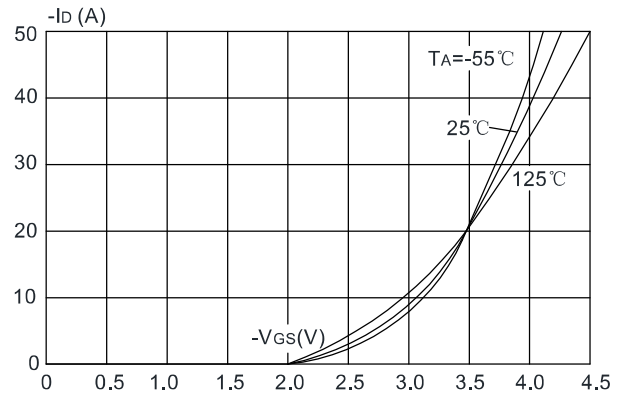


Figure 3: On-resistance vs. Drain Current

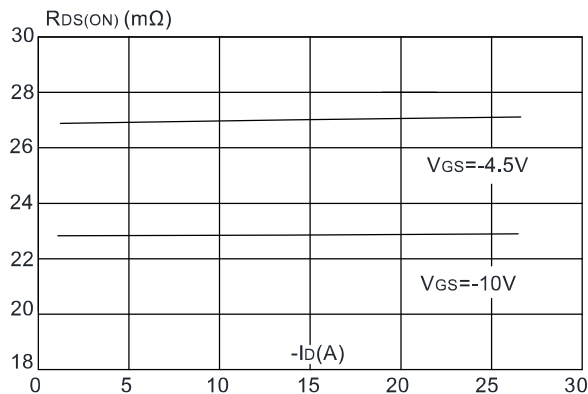


Figure 4: Body Diode Characteristics

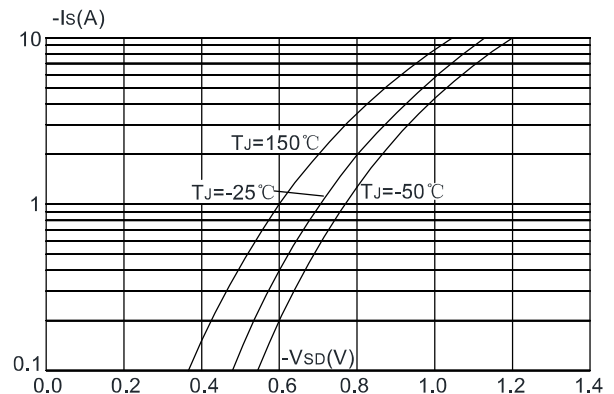


Figure 5: Gate Charge Characteristics

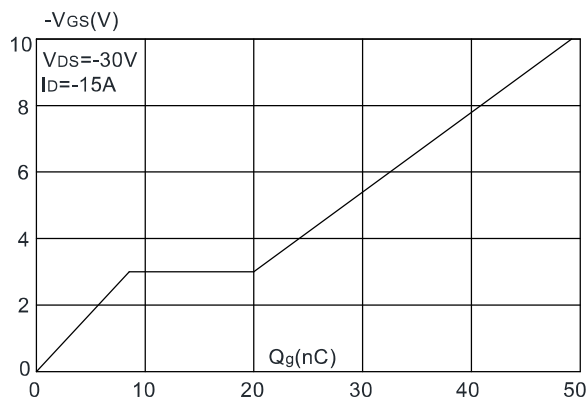


Figure 6: Capacitance Characteristics

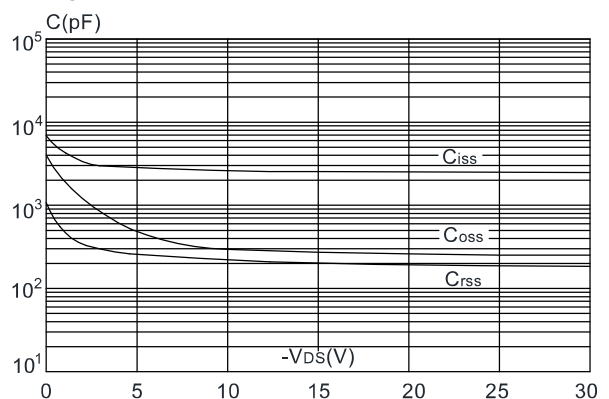


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

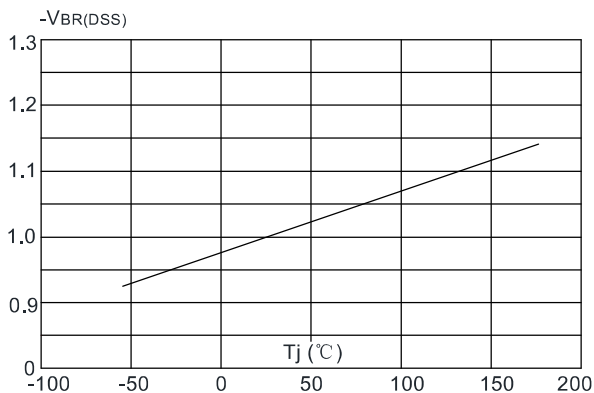


Figure 8: Normalized on Resistance vs. Junction Temperature

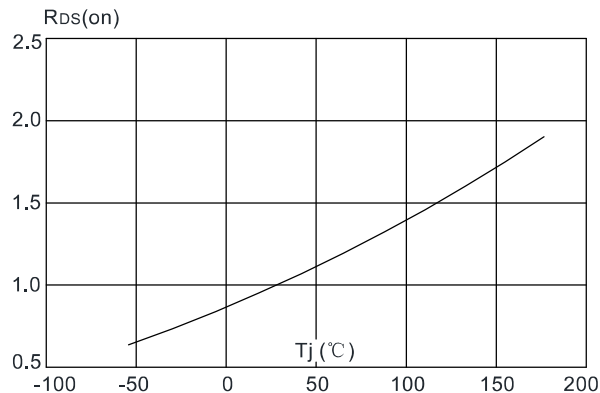


Figure 9: Maximum Safe Operating Area

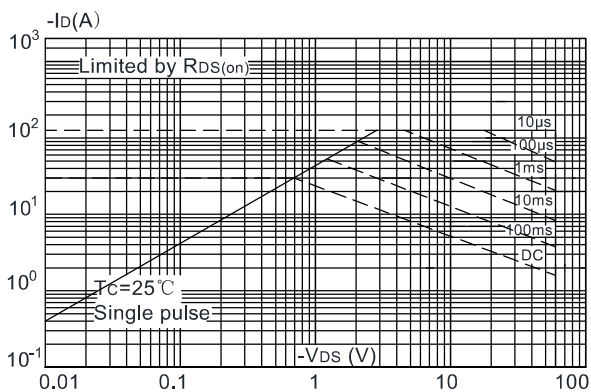


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

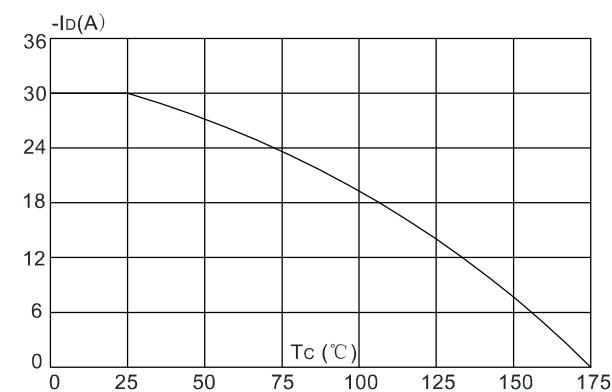
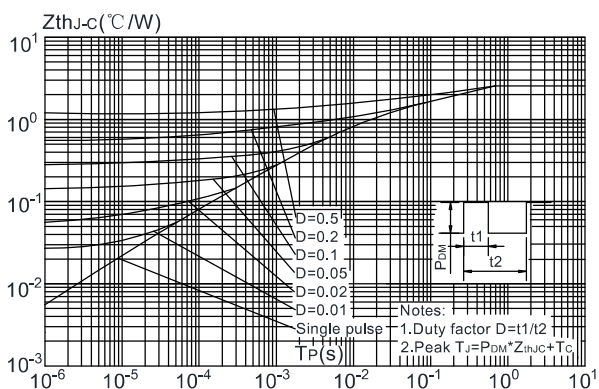


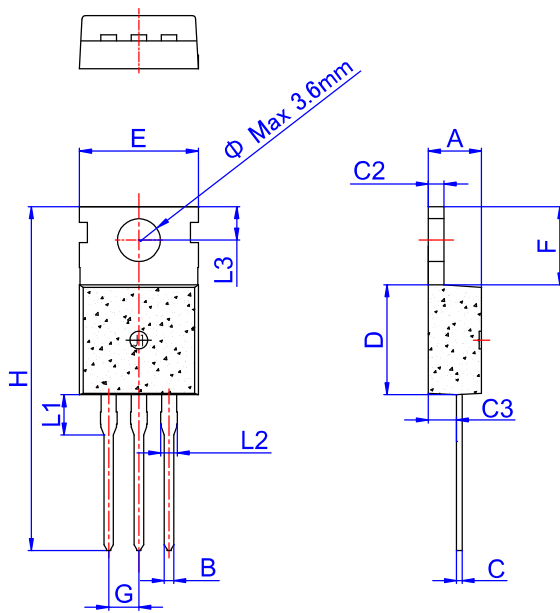
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



AP30P06

P-Channel Enhancement Mosfet

TO-220C Package Information



TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

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